in Figure 4 was obtained.

On page 7, replace the third full paragraph with the following:

Thus the full-width at half maximum shown in Figure 5 is generally a value of 1 or more. It can further be seen that as the value approaches 1, the construction approaches a monocrystalline construction. As can be seen from Figure 5, it is possible to obtain a crystallinity which approaches that of a monocrystal if the temperature to which the sample is heated during irradiation with laser light is increased. It can further be seen that the effects due to heating the sample become saturated at about 500°C.

On page 8, replace the second full paragraph with the following:

In the opinion of the present inventors, a region can be regarded as being monocrystalline if the Raman intensity shown in Figure 4 is 0.8 or more, the full-width at half maximum of the Raman spectrum shown in Figure 5 is 2.0 or less, and there are effectively no crystal grain boundaries within the region.

Page 13, replace the fifth full paragraph with the following:

Figure 5 shows the relationship between the energy density of laser light irradiation and the full-width at half maximum of the Raman spectrum for cases in which the temperature to which the sample is heated varies.

IN THE CLAIMS:

Please cancel claims 6, 26-28, 48, 49, 63 and 74 without prejudice or disclaimer of the subject matter recited therein.

Please amend claims 1-3 and 8 as follows. Attached hereto is a marked-up copy of the amended claims.

1. (Amended) An active matrix type display device comprising:

at least two transistors provided on an insulating surface in a XY-branching circuit of a peripheral circuit of said active matrix type display device;

a common gate wiring provided on said insulating surface and connected with said at least two transistors at gate electrodes of said at least two transistors;